Ordering number : ENN7509

PNP Epitaxial Planar Silicon Transistor

30A01C

Low-Frequency General-Purpose Amplifier Applications

Applications

- Low-frequency power amplifier, muting circuit.

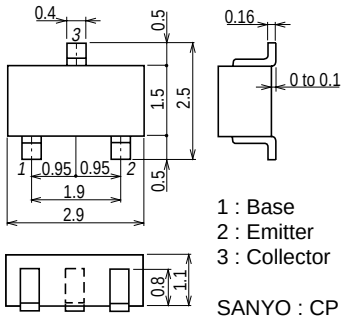
Features

- Large current capacity.
- Low collector-to-emitter saturation voltage (resistance). R_{CE}(sat) typ=0.67Ω[I_C=0.3A, I_B=15mA].
- Ultrasmall package facilitates miniaturization in end products.
- Small ON-resistance (Ron).

Package Dimensions

unit : mm
2018B

[30A01C]



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		–30	V
Collector-to-Emitter Voltage	V_{CEO}		–30	V
Emitter-to-Base Voltage	V_{EBO}		–5	V
Collector Current	I_C		–300	mA
Collector Current (Pulse)	I_{CP}		–600	mA
Collector Dissipation	P_C	Mounted on a glass epoxy board (20×30×1.6mm).	300	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		–55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=–30V, I_E=0			–0.1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=–4V, I_C=0			–0.1	μA
DC Current Gain	h_{FE}	V_{CE}=–2V, I_C=–10mA	200		500	
Gain-Bandwidth Product	f_T	V_{CE}=–10V, I_C=–50mA		520		MHz
Output Capacitance	Cob	V_{CB}=–10V, f=1MHz		3		pF
Collector-to-Emitter Saturation Voltage	V_{CE}(sat)	I_C=–100mA, I_B=–5mA		–110	–220	mV
Base-to-Emitter Saturation Voltage	V_{BE}(sat)	I_C=–100mA, I_B=–5mA		–0.9	–1.2	V

Marking : XQ

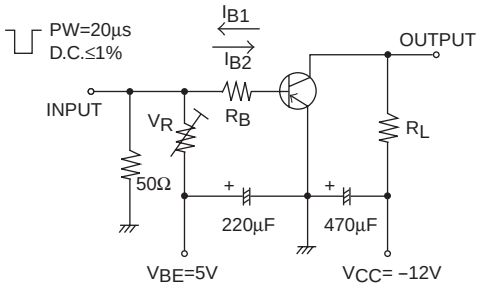
Continued on next page.

SANYO Electric Co.,Ltd. Semiconductor Company
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

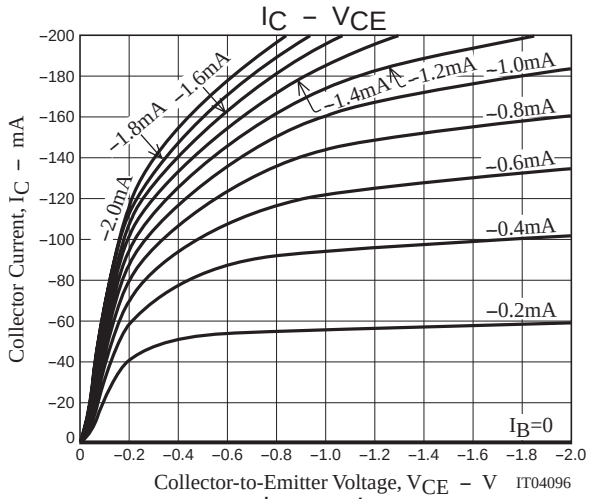
Continued from preceding page.

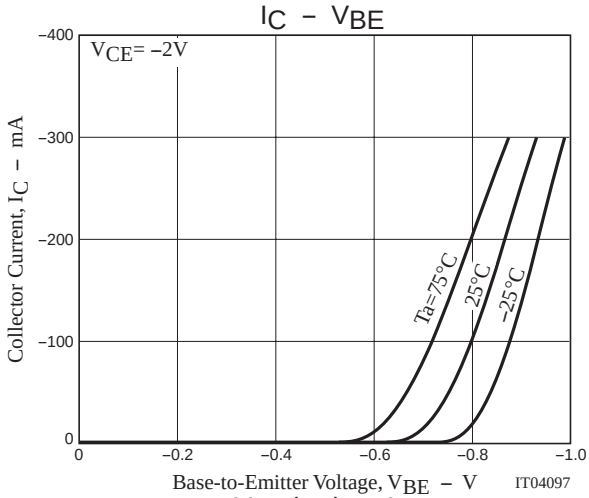
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=–10μA, I_E=0	–30			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=–1mA, R_{BE}=∞	–30			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=–10μA, I_C=0	–5			V
Turn-ON Time	t_{on}	See specified Test Circuit.		39		ns
Storage Time	t_{stg}	See specified Test Circuit.		200		ns
Fall Time	t_f	See specified Test Circuit.		48		ns

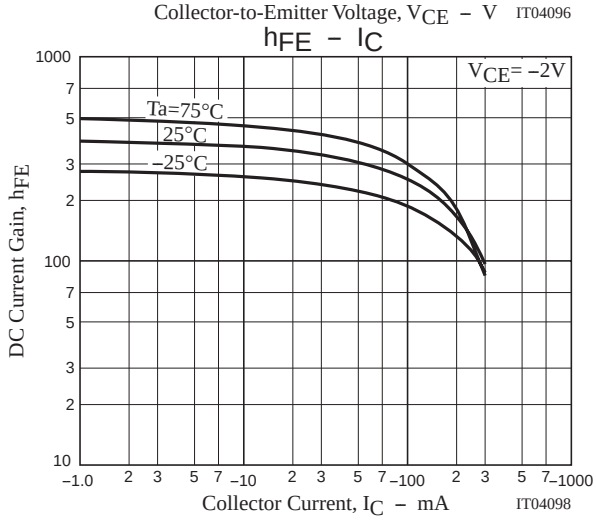
Switching Time Test Circuit

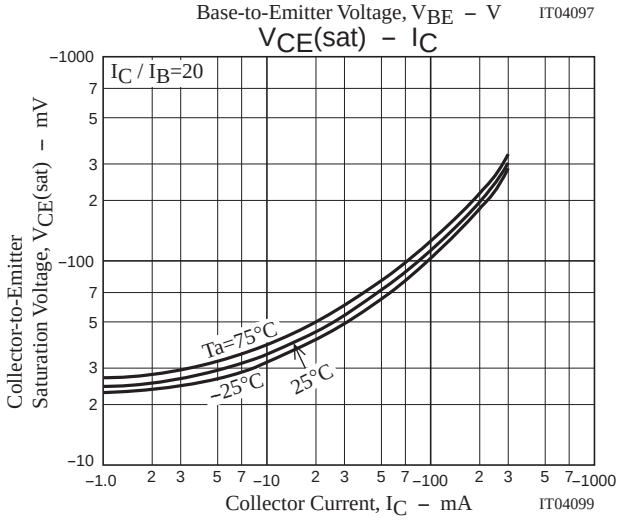


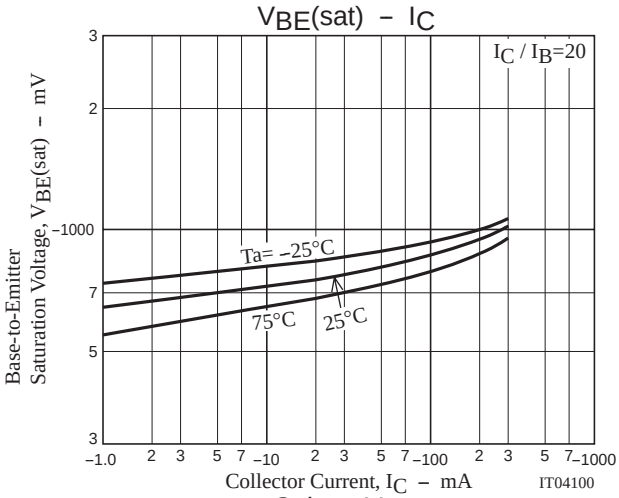
I_C=20I_{B1}= –20I_{B2}= –100mA

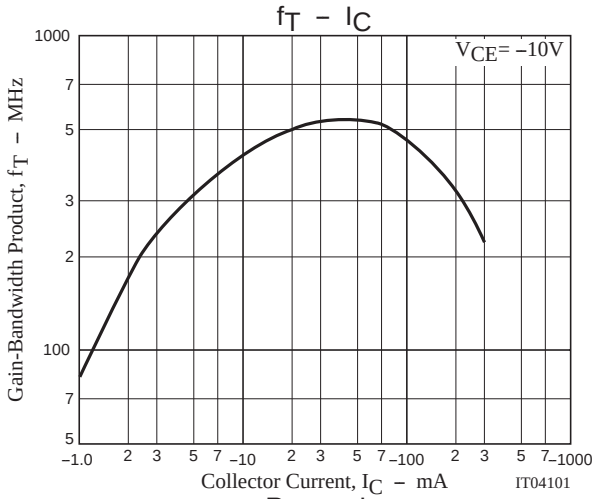


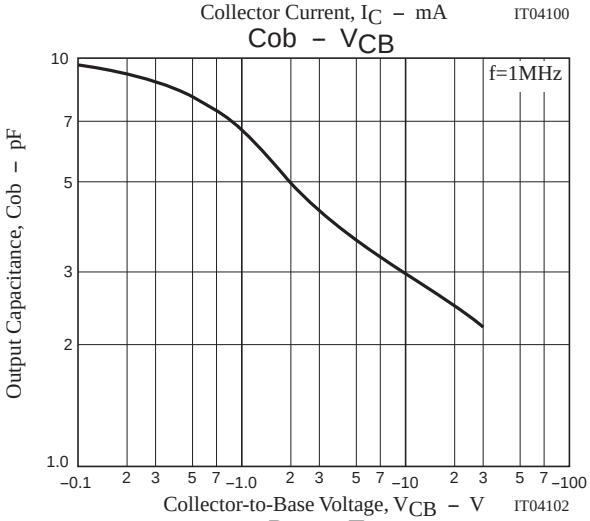


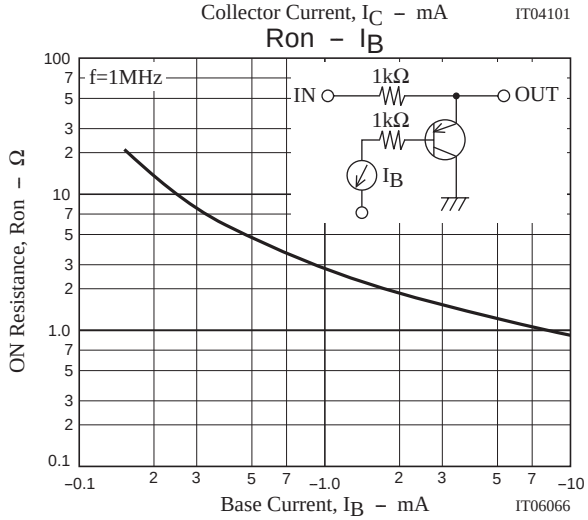


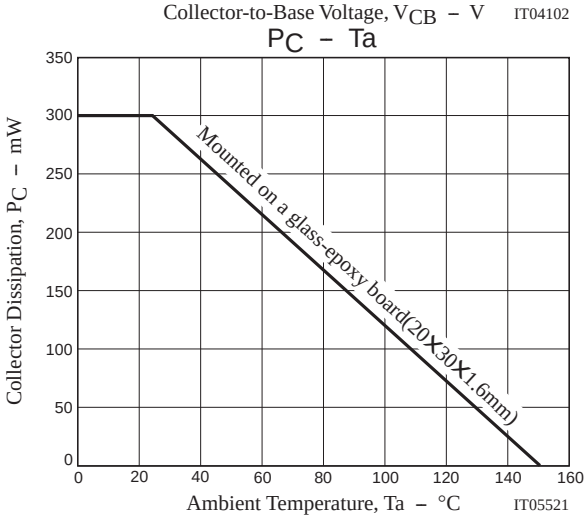



VBE(sat) – IC
IC / IB=20
Ta= –25°C
75°C
25°C
Base-to-Emitter Saturation Voltage, VBE(sat) – mV
Collector Current, IC – mA
IT04100


fT – IC
VCE= –10V
Gain-Bandwidth Product, fT – MHz
Collector Current, IC – mA
IT04101


Cob – VCB
f=1MHz
Output Capacitance, Cob – pF
Collector-to-Base Voltage, VCB – V
IT04102


Ron – IB
f=1MHz
IN
1kΩ
1kΩ
OUT
IB
ON Resistance, Ron – Ω
Base Current, IB – mA
IT06066


PC – Ta
Mounted on a glass-epoxy board(20x30x1.6mm)
Collector Dissipation, PC – mW
Ambient Temperature, Ta – °C
IT05521

- Specifications of any and all SANYO products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- SANYO Electric Co., Ltd. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all SANYO products(including technical data,services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of SANYO Electric Co., Ltd.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the SANYO product that you intend to use.
- Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. SANYO believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

This catalog provides information as of October, 2003. Specifications and information herein are subject to change without notice.